

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

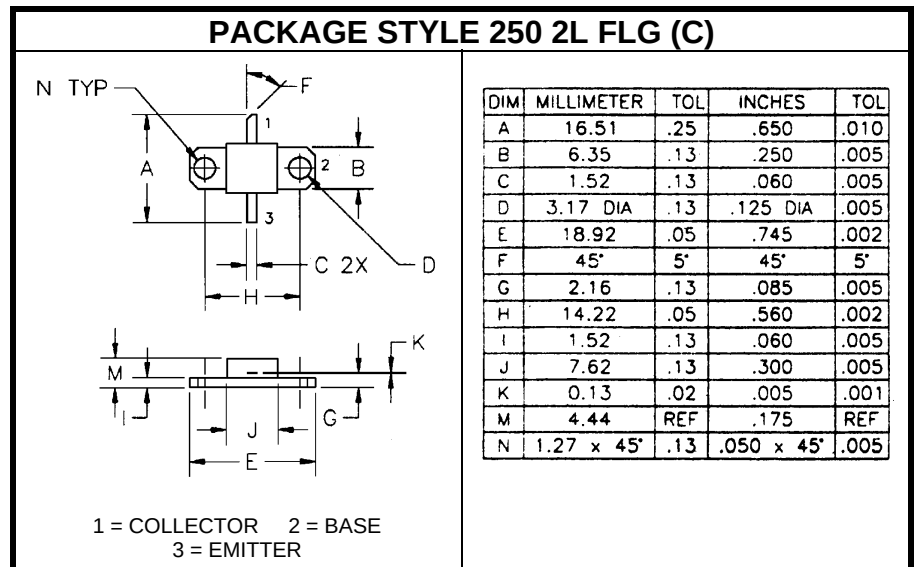
The **ASI MRA1417-11** is a Common Base Device Designed for Class C Power Amplifier Applications up to 1.7 GHz.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	50 V
P_{DISS}	12 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	4.5°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 80\text{ mA}$	50			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
I_{CBO}	$V_{CB} = 28\text{ V}$			2.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 4.0\text{ A}$	10		100	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			12	pF
P_G	$V_{CE} = 28\text{ V}$ $P_{OUT} = 11\text{ W}$ $f = 1700\text{ MHz}$	7.4			dB
η_C		45			%